

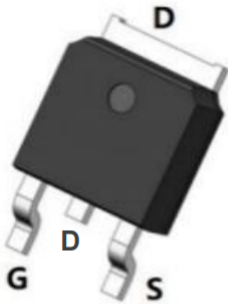
Product Summary

- V_{DS} 60 V
- I_{DS} 80A
- $R_{DS(ON)}$ (at $V_{GS}=10$) $\leq 6.6m\Omega$ (Typ)
- Low Gate Charge Minimize Switching Loss

Application

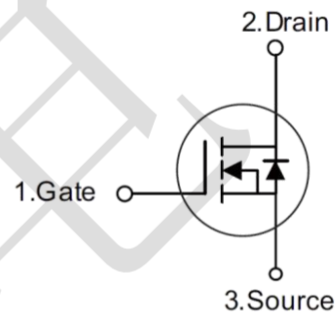
- Adaptor
- Charger
- Power management
- SMPS Standby Power

Package and Pin Configuration



T0-252

Circuit diagram



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	80	A
Continuous Drain Current ($T_C=100^\circ\text{C}$)	I_D	56	A
Pulsed Drain Current (Note 1)	I_{DM}	240	A
Maximum Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	68	W
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	225	mJ
Operating Junction Temperature Range	T_J	+150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Note : 1.When mounted on 1" square PCB (FR4 material).

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$

Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	BV _{DSS}	60	--	--	V
Gate-Source Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	V _{GS(th)}	1.2	1.7	2.2	V
Gate-Source Leakage	V _{DS} =0V, V _{GS} = ±20V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} =0V	I _{DSS}	--	--	1	μA
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 30A	R _{DS(on)}	--	6.6	8.0	mΩ
	V _{GS} = 4.5V, I _D = 30A		--	9.3	11	
Forward Trans conductance	V _{DS} =5V,I _D =30A	g _{FS}	--	30	--	S
Dynamic (Note 2)						
Total Gate Charge (Note 3)	V _{DS} = 30V, I _D =20A, V _{GS} = 10V	Q _g	--	31	--	nC
Gate-Source Charge (Note 3)		Q _{gs}	--	6.0	--	
Gate-Drain Charge (Note 3)		Q _{gd}	--	5.0	--	
Input Capacitance	V _{DS} = 30V, V _{GS} = 0V, F= 1.0MHz	C _{iss}	--	1990	--	pF
Output Capacitance		C _{oss}	--	470	--	
Reverse Transfer Capacitance		C _{rss}	--	14	--	
Switching						
Turn-On Delay Time (Note 3)	V _{DD} = 30V, I _D = 2A, V _{GS} = 10V, R _G = 3Ω	t _{d(on)}	--	16	--	nS
Rise Time (Note 3)		t _r	--	8.0	--	
Turn-Off Delay Time (Note 3)		t _{d(off)}	--	45	--	
Fall Time (Note 3)		t _f	--	33	--	
Source-Drain Diode Ratings and Characteristics (Note 2)						
Forward Voltage	V _{GS} = 0V, I _S = 10A	V _{SD}	--	0.8	1.2	V
Continuous Source Current	Integral reverse diode in the MOSFET	I _S	--	--	80	A
Pulsed Current (Note 1)		I _{SM}	--	--	240	A

Notes:

1. Pulse test; pulse width ≤ 300 μS, duty cycle ≤ 1%.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

TYPICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig. 1-Output Characteristics

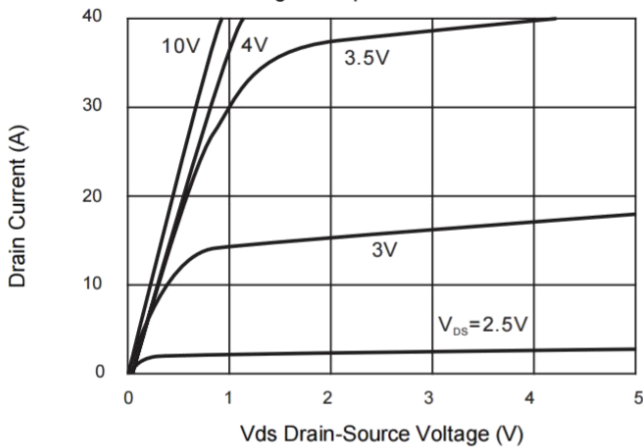


Fig. 2-Rdson-Junction Temperature

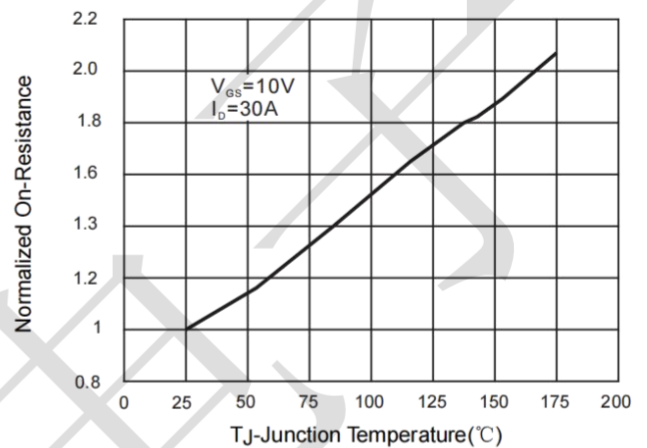


Fig. 3-Transfer Characteristics

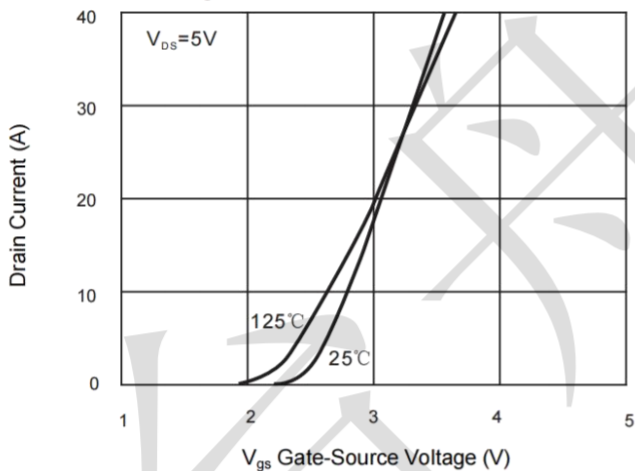


Fig. 4 - Total Gate Charge Characteristics

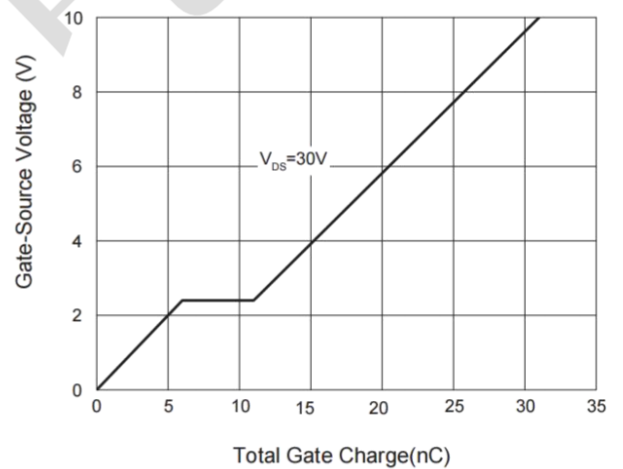


Fig. 5-Rdson- Drain Current

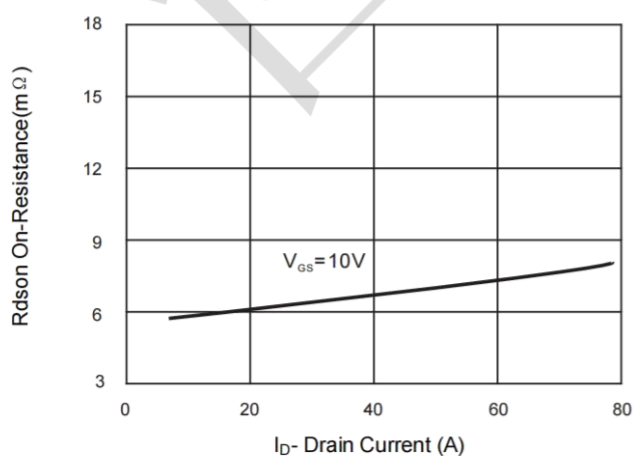
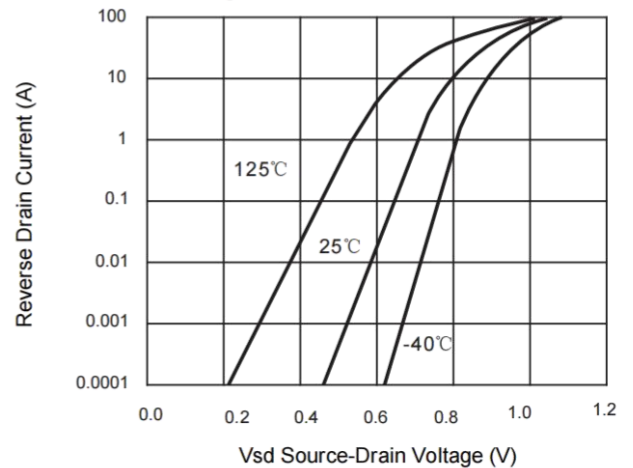
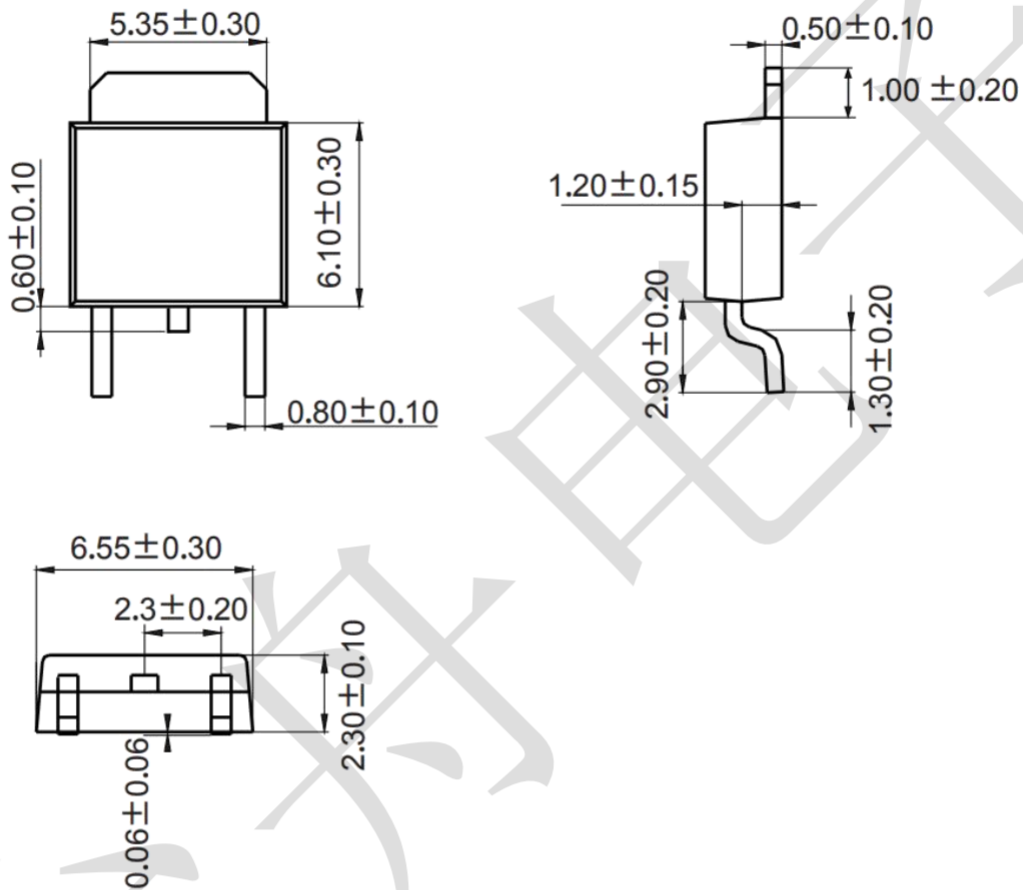


Fig. 6-Source- Drain Diode Forward



Package Outline Dimensions (unit: mm)

TO-252



Mounting Pad Layout (unit: mm)

